2SB1530

Silicon PNP Triple Diffused

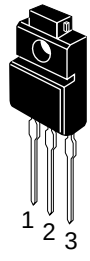
HITACHI

Application

Low frequency power amplifier color TV vertical deflection output complementary pair with 2SD2337

Outline

TO-220FM



1. Base
2. Collector
3. Emitter

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Absolute Maximum Ratings (Ta = 25°C)

Item	Symbol	Ratings	Unit
Collector to base voltage	V_{CBO}	–200	V
Collector to emitter voltage	V_{CEO}	–150	V
Emitter to base voltage	V_{EBO}	–6	V
Collector current	I_C	–2	A
Collector peak current	$I_{C(peak)}$	–5	A
Collector power dissipation	P_C	1.5	W
	P_C*[1]	20	
Junction temperature	Tj	150	°C
Storage temperature	Tstg	–45 to +150	°C

Note: 1. Value at T_C = 25°C.

Electrical Characteristics (Ta = 25°C)

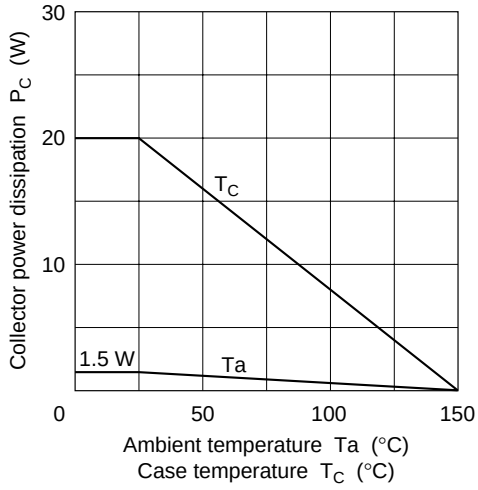
Item	Symbol	Min	Typ	Max	Unit	Test conditions
Collector to emitter breakdown voltage	$V_{(BR)CEO}$	–150	—	—	V	I_C = –50 mA, R_{BE} = ∞
Emitter to base breakdown voltage	$V_{(BR)EBO}$	–6	—	—	V	I_E = –5 mA, I_C = 0
Collector cutoff current	I_{CBO}	—	—	–1	µA	V_{CB} = –120 V, I_E = 0
DC current transfer ratio	h_{FE1}*[1]	60	—	200		V_{CE} = –4 V, I_C = –50 mA
	h_{FE2}	60	—	—		V_{CE} = –10 V, I_C = –500 mA*[2]
Collector to emitter saturation voltage	$V_{CE(sat)}$	—	—	–3	V	I_C = –500 mA, I_B = –50 mA
Base to emitter voltage	V_{BE}	—	—	–1	V	I_{CE} = –4 A, I_C = –50 mA

Notes: 1. The 2SB1530 is grouped by h_{FE1} as follows.

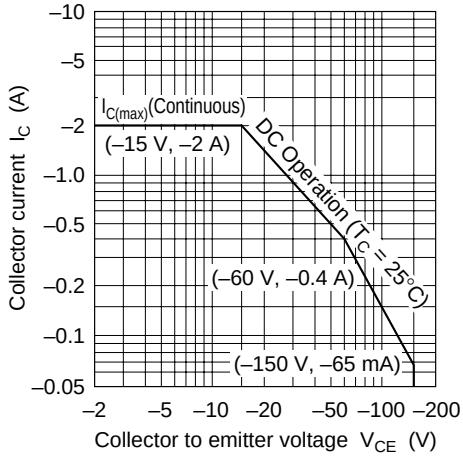
B	C
60 to 120	100 to 200

2. Pulse test.

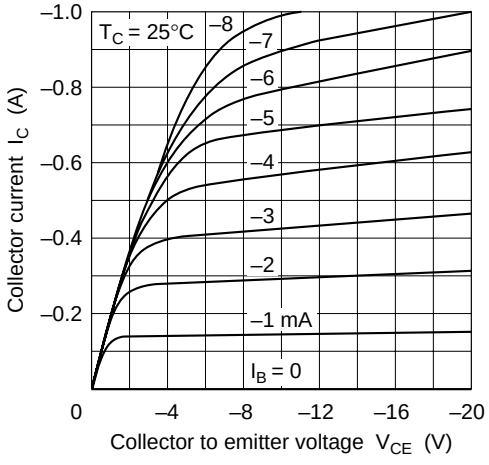
Maximum Collector Dissipation Curve



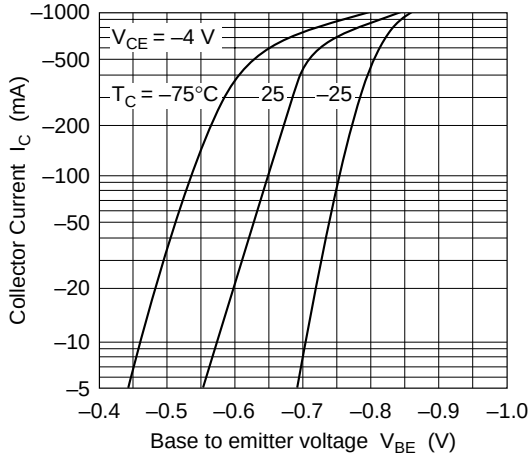
Area of Safe Operation



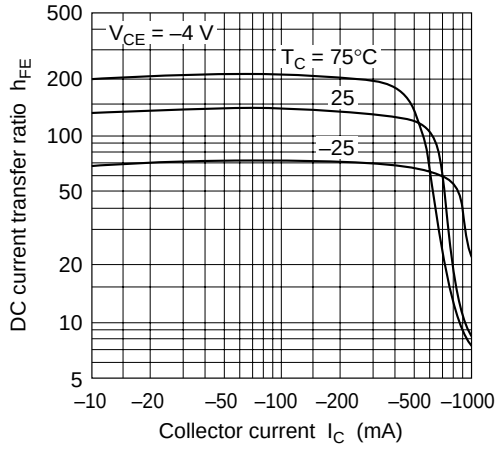
Typical Output Characteristics



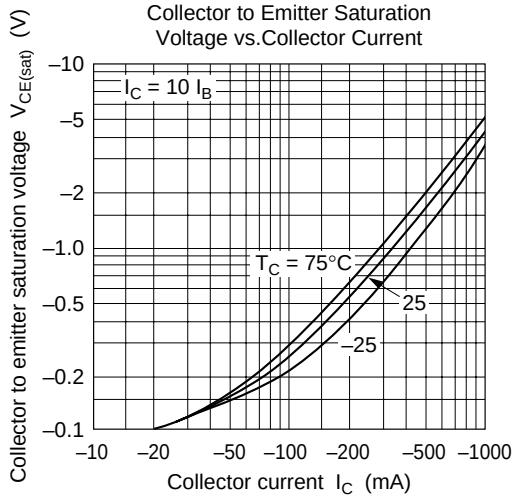
Typical Output Characteristics



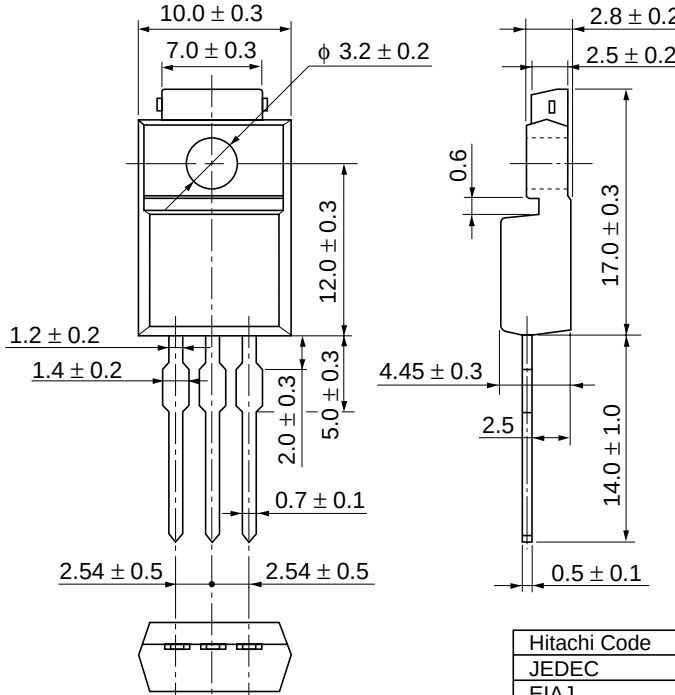
DC Current Transfer Ratio vs. Collector Current

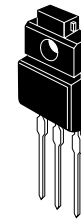


Collector to Emitter Saturation Voltage vs.Collector Current



Unit: mm





Hitachi Code	TO-220FM
JEDEC	—
EIAJ	Conforms
Weight (reference value)	1.8 g

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